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OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)										
GL		A Novel-Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-scale Memories by Farid Nemati and James D. Plummer, Center for Integrated Systems, Stanford, University, 1999								
W		A Novel High De	A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device, by Farid Nemati and							
		James D. Plummer, Center for Integrated Systems, Stanford University, 1998								
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